

Lonten N-channel 650V, 78A, 0.041Ω LonFET[™] Power MOSFET

Description

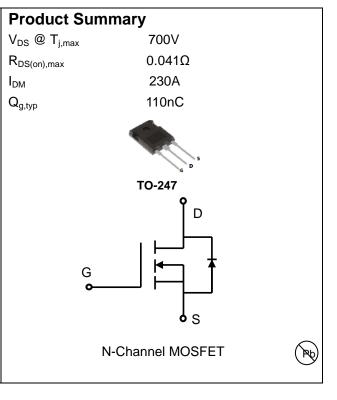
LonFETTM Power MOSFET is fabricated using advanced super junction technology. The resulting device has extremely low on resistance, making it especially suitable for applications which require superior power density and outstanding efficiency.

Features

- ◆ Ultra low R_{DS(on)}
- ◆ Ultra low gate charge (typ. Q_g = 110nC)
- ♦ 100% UIS tested
- RoHS compliant

Applications

- Power faction correction (PFC).
- Switched mode power supplies (SMPS).
- Uninterruptible power supply (UPS).



Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	650	V
Continuous drain current (T _C = 25°C)	I _D	78	Α
(T _C = 100°C)		46	Α
Pulsed drain current 1)	I _{DM}	230	Α
Gate-Source voltage	V_{GSS}	±30	V
Avalanche energy, single pulse 2)	E _{AS}	2350	mJ
Power Dissipation TO-247 (T _C = 25°C)	P _D	500	W
- Derate above 25°C	FD	4.0	W/°C
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C
Continuous diode forward current	Is	78	Α
Diode pulse current	I _{S,pulse}	230	Α

Thermal Characteristics TO-247

Parameter	Symbol	Value	Unit	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.25	°C/W	
Thermal Resistance, Junction-to-Ambient	R _{0JA}	62	°C/W	
Soldering temperature, wavesoldering only allowed	260	°C		
at leads. (1.6mm from case for 10s)	I sold	260		



Package Marking and Ordering Information

Device	Device Package	Marking	Units/Tube	Units/Real
LSB65R041GT	TO-247	LSB65R041GT	30	

Electrical Characteristics T_c = 25°C unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Static characteristics			<u>.</u>			
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0 V, I _D =0.25 mA	650	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V _{DS} =V _{GS} , I _D =0.25 mA	2.5	3.0	4.5	V
Drain cut-off current	I _{DSS}	V _{DS} =650 V, V _{GS} =0 V,				μΑ
		T _j = 25°C	-	-	1	
		T _j = 125°C	-	10	-	
Gate leakage current, Forward	I _{GSSF}	V _{GS} =30 V, V _{DS} =0 V	-	-	100	nA
Gate leakage current, Reverse	I _{GSSR}	V _{GS} =-30 V, V _{DS} =0 V	-	-	-100	nA
Drain-source on-state resistance	R _{DS(on)}	V _{GS} =10 V, I _D =39 A	-			
		T _j = 25°C	-	0.036	0.041	Ω
		T _j = 150°C	-	0.094	-	
Dynamic characteristics						
Input capacitance	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V,	-	6000	-	
Output capacitance	C _{oss}	f = 1 MHz	-	4800	-	pF
Reverse transfer capacitance	C _{rss}]	-	35	-	
Turn-on delay time	t _{d(on)}	$V_{DD} = 400 \text{ V}, I_D = 39 \text{ A}$	-	46	-	
Rise time	t _r	$R_G = 10 \Omega, V_{GS}=10 V$	-	52	-	ns
Turn-off delay time	t _{d(off)}		-	342	-	•
Fall time	t _f		-	8.6	-	•
Gate charge characteristics	<u></u>	1				I
Gate to source charge	Q_{gs}	V _{DD} =400 V, I _D =39 A,	-	25.7	-	
Gate to drain charge	Q_{gd}	V _{GS} =0 to 10 V	-	42.2	-	nC
Gate charge total	Q _g		-	110	-	
Gate plateau voltage	V _{plateau}		-	6.0	-	V
Reverse diode characteristics		1		l.	l.	
Diode forward voltage	V _{SD}	V _{GS} =0 V, I _F =39 A	-	-	1.2	V
Reverse recovery time	t _{rr}	V _R =50 V, I _F =39 A,	-	594	-	ns
Reverse recovery charge	Q _{rr}	dI _F /dt=100 A/µs	-	8.5	-	μC
Peak reverse recovery current	I _{rrm}	1	-	29	-	Α

Notes:

^{1.} Limited by maximum junction temperature, maximum duty cycle is 0.75.

^{2.} I_{AS} = 10A, V_{DD} =60V, Starting T_j = 25°C.



Electrical Characteristics Diagrams

Figure 1. On-Region Characteristics

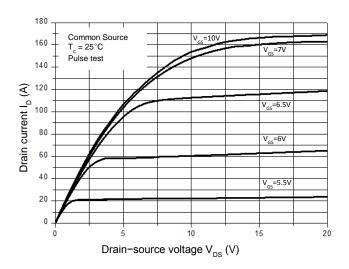


Figure 3. On-Resistance Variation vs. Drain Current

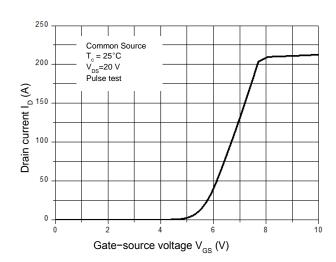


Figure 2. Transfer Characteristics

Figure 4. Threshold Voltage vs. Temperature

1.3

1.2

1.1

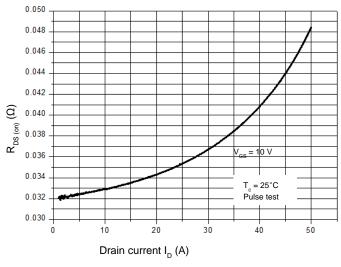
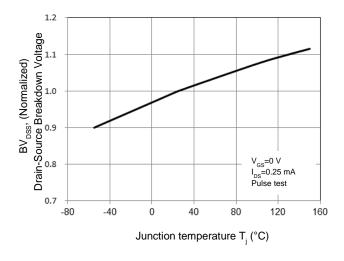


Figure 5. Breakdown Voltage vs. Temperature



(Section 1)

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Figure 6. On-Resistance vs. Temperature

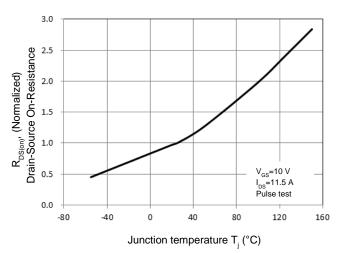




Figure 7. Capacitance Characteristics

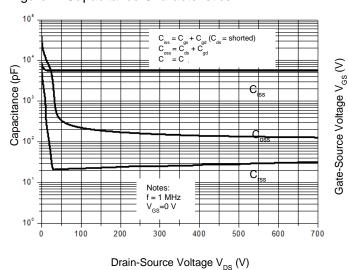


Figure 8. Gate Charge Characterist

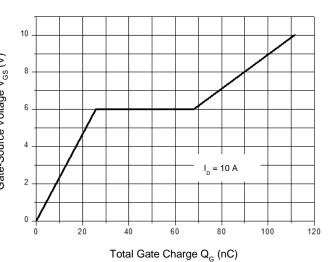


Figure 9 Maximum Safe Operating Area

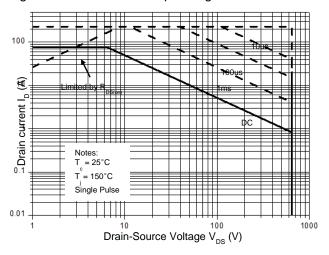
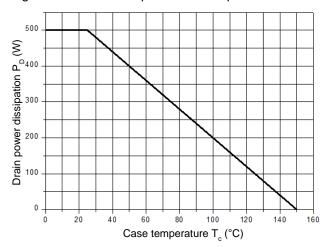
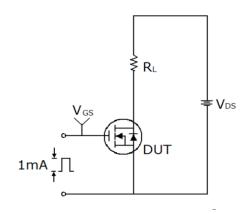


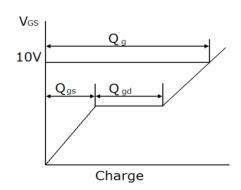
Figure 10 Power Dissipation vs. Temperature

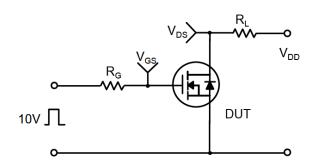


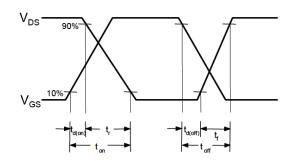


Gate Charge Test Circuit & Waveform

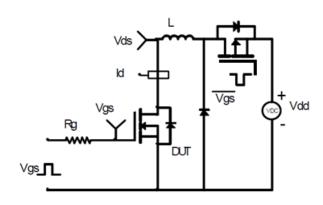


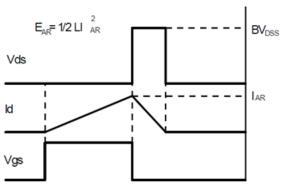






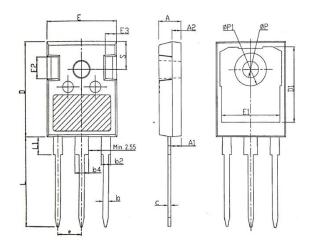
Unclamped Inductive Switching Test Circuit & Waveforms





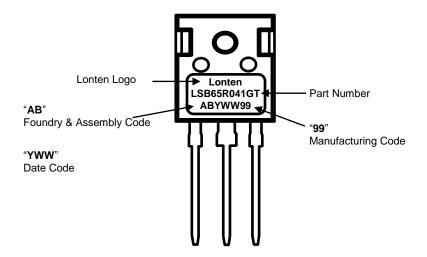


Mechanical Dimensions for TO-247



SYMBOL	mm		
STIVIBOL	MIN	NOM	MAX
Α	4.80	5.00	5.20
A1	2.21	2.41	2.59
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
С	0.51	0.61	0.75
D	20.80	21.00	21.30
D1	16.25	16.55	16.85
Е	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30 2.50		2.70
е	5.44BSC		
L	19.82	19.92	20.22
L1	_	_	4.30
ØP	3.40	3.60	3.80
ØP1	_	_	7.30
S	6.15BSC		

TO-247 Part Marking Information





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